

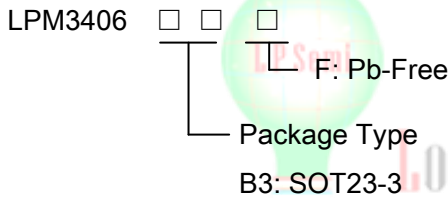


# 30V/3.6A N-Channel Enhancement Mode Field Effect Transistor

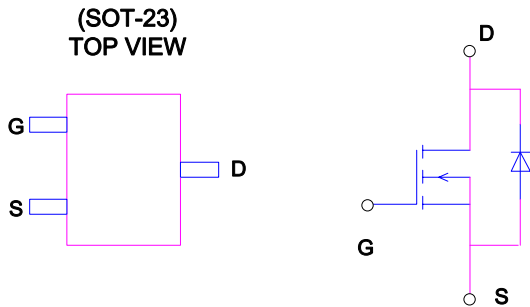
## General Description

The LPM3406 is N-channel logic enhancement mode power field effect transistor, which are produced by using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suitable for low voltage applications, notebook computer power management and other battery powered circuits where high-side switching is needed.

## Order Information



## Pin Configurations



## Features

- ◆ 30V/3A,  $R_{DS(ON)}=48m\Omega(Typ.)@VGS=4.5V$
- ◆ 30V/3.6A,  $R_{DS(ON)}=36m\Omega(Typ.)@VGS=10V$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ SOT23 Package

## Applications

- ✧ Portable Media Players/MP3 players
- ✧ Cellular and Smart mobile phone
- ✧ LCD
- ✧ DSC Sensor
- ✧ Wireless Card

## Marking Information

Device	Marking	Package	Shipping
LPM3406B3F	LPS M6YWX	SOT23	3K/REEL
Marking indication: Y:Production year W:Production week X:Production batch			

## Pin Description

Pin Number	Pin Description
1	Gate Pin
2	Source Pin
3	Drain Pin



## Absolute Maximum Ratings

Absolute Maximum Ratings TA=25°C Unless Otherwise noted				
Parameter		Symbol	Maximum	Units
Drain-Source Voltage		VDS	30	V
Gate-Source Voltage		VGS	±20	V
Continuous Drain Current	TA=25°C	ID	3.6	A
	TA=70°C		2.9	
Pulsed Drain Current		IDM	15	
Power Dissipation	TA=25°C	PD	1.4	W
	TA=70°C		0.9	
Junction and Storage Temperature Range		TJ, TSTG	-55 to 150	°C
Thermal Characteristics				
Parameter		Symbol	Typ.	Units
Maximum Junction-to-Ambient		RθJA	125	°C/W



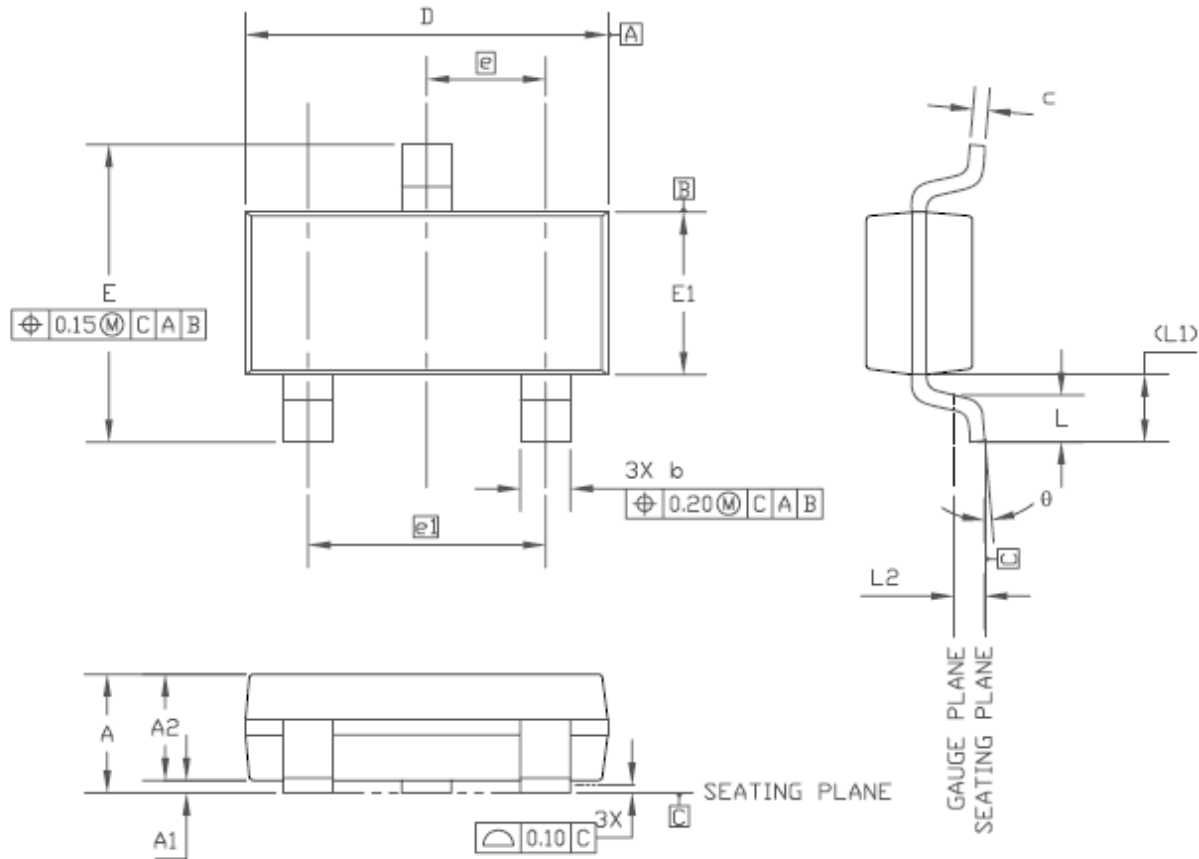
## Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
<b>STATIC PARAMETER</b>						
BVDSS	Drain-Source Breakdown Voltage	ID=250μ A , VGS=0V	30			V
IDSS	Zero-Gate Voltage Drain Current	VDS=16V,VGS=0V TJ=55°C			1 5	μA
IGSS	Gate-Body Leakage Current	VDS=0V,VGS=±8V			100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=250μA	1	1.8	2.5	V
RDS(ON)	Static Drain-Source On-Resistance	VGS=10V, ID=3.6A TJ=125°C		36		mΩ
		VGS=4.5V, ID=3A		58		mΩ
gFs	Forward Transconductance	VDS=5V,ID=3A		11		S
VSD	Diode Forward Voltage	IS=1A,VGS=0V		0.76	1	V
IS	Maximum Body-Diode Continuous Current				1.5	A
<b>DYNAMIC PARAMETERS</b>						
Ciss	Input Capacitance	VDS=10V,VGS=0V f = 1MHz		180		pF
Coss	Output Capacitance			35		pF
Crss	Reverse Transfer Capacitance			23		pF
Rg	Gate Resistance	VDS=0V,VGS=0V f = 1MHz		3.5		Ω
<b>SWITCHING PARAMETERS</b>						
Qg	Total Gate Charge	VDS=10V,VGS=4.5V ID=3A		4.1		nC
Qgs	Gate Source Charge			0.55		nC
Qgd	Gate Drain Charge			1		nC
tD(ON)	Turn-On Delay Time	VDS=10V,VGS=5V RL=2.7Ω		4.5		nS
tr	Turn-On Rise Time			1.5		nS
tD(OFF)	Turn-Off Delay Time			18.5		nS
tf	Turn-Off Fall Time			15.5		nS
trr	Body-Diode Reverse Recovery Time	IF=3A,d I/dt=100/μS		7.5		nS
Qrr	Body-Diode Reverse Recovery Charge	IF=3A,d I/dt=100/μS		2.5		nC

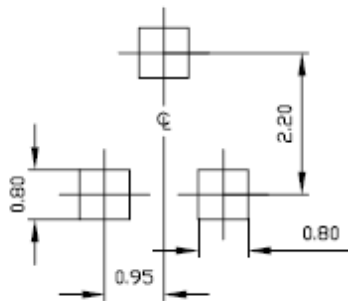


## Packaging Information

### SOT-23 STANDARD PACKAGE OUTLINE



#### RECOMMENDED LAND PATTERN



UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.75	—	1.17	0.030	—	0.046
A1	0.05	—	0.15	0.002	—	0.006
A2	0.70	0.85	1.02	0.028	0.033	0.040
b	0.30	—	0.50	0.012	—	0.020
c	0.08	—	0.20	0.003	—	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	2.10	—	2.64	0.083	—	0.104
E1	1.20	1.30	1.40	0.047	0.051	0.055
e	0.95 BSC			0.037 BSC		
e1	1.90 BSC			0.075 BSC		
L	0.40	0.50	0.60	0.016	0.020	0.024
L1	0.54 REF			0.021 REF		
L2	0.25			0.010		
$\theta$	0°	—	8°	0°	—	8°